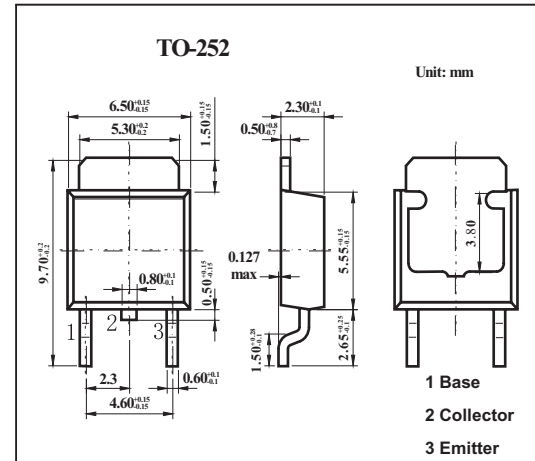


AF Power Amplifier Applications

2SB1266

■ Features

- Suitable for sets whose height is restricted.
- High reliability.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-60	V
Collector-emitter voltage	V_{CEO}	-60	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-3	A
Collector current (pulse)	I_{CP}	-8	A
Collector dissipation	P_C	1.65	W
$T_C = 25^\circ\text{C}$		30	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -40\text{V}$, $I_E = 0$			-100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -4\text{V}$, $I_C = 0$			-100	μA
DC current Gain	h_{FE}	$V_{CE} = -5\text{V}$, $I_C = -0.5\text{A}$	70		280	
		$V_{CE} = -5\text{V}$, $I_C = -3\text{A}$	20			
Gain bandwidth product	f_T	$V_{CE} = -5\text{V}$, $I_C = -0.5\text{A}$		8		MHz
Output capacitance	C_{ob}	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}$		60		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{A}$, $I_B = -0.2\text{A}$		-0.4	-1	V
Base-emitter voltage	V_{BE}	$I_C = -5\text{V}$, $I_C = -0.5\text{A}$		-0.7	-1	V
Collector-to-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1\text{mA}$, $I_E = 0$	-60			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -5\text{mA}$, $R_{BE} = \infty$	-60			V
Emitter-to-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1\text{mA}$, $I_C = 0$	-6			V

■ h_{FE} Classification

Rank	Q	R	S
h_{FE}	70~140	100~200	140~280